

IN THE ABSTRACT OF THE DISCLOSURE

Amend the Abstract as follows:

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~~There is disclosed a method for fabricating~~
~~semiconductor~~ Semiconductor devices having a wiring
construction consisting of a conductive layer (a copper layer)
and an insulating layer (a porous insulator layer with low
dielectric constant) are fabricated. A method for forming
wiring ~~forming~~ of semiconductor devices of the present
~~invention comprises at least: a~~ includes a first step for
forming a first insulating material layer on a sample; a
second step for forming ~~on the first insulating material layer~~
a second insulating material layer with a dielectric constant
less than 2.5; a third step for patterning the second
insulating material layer by a plasma etching method; a fourth
step for depositing a metal film on the second insulating
material layer by a sputtering method; a fifth step for
forming a copper layer on the metal film; and a sixth step for
removing an unnecessary portion of the copper layer by
Chemical Mechanical Polishing, wherein all the processes from
the third to the fourth step are performed under drying
process conditions, ~~and a pure water treatment for cleaning~~
~~the sample with pure water is provided after the sixth step.~~
~~The wiring forming method of the present invention can form a~~

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B/at ~~good semiconductor device wiring having high reliability.~~

IN THE TITLE

Amend the title to -- A METHOD FOR FABRICATING
SEMICONDUCTOR DEVICES INCLUDING WIRING FORMING WITH A POROUS
LOW-K FILM AND COPPER --.